

1.5V Drive Nch MOSFET RQ1C065UN

Structure

Silicon N-channel MOSFET

Features

1) Low on-resistance.

- 2) High power package(TSMT8).
- 3) Low voltage drive(1.5V drive).

Application

Switching

Packaging specifications

Туре	Package	Taping
	Code	TR
	Basic ordering unit (pieces)	3000
RQ1C065L	JN	0

• Absolute maximum ratings (Ta = 25°C)

	• •	/		
Paran	neter	Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	20	V
Gate-source voltage		V _{GSS}	±10	V
Drain current	Continuous	I _D	±6.5	А
Drain current	Pulsed	ا _{DP} *1	±26	А
Source current	Continuous	۱ _s	1	А
(Body Diode)	Pulsed	ا _{SP} *1	26	А
Power dissipation		P _D *2	1.5	W
Channel temperature		Tch	150	°C
Range of storage terr	perature	Tstg	-55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

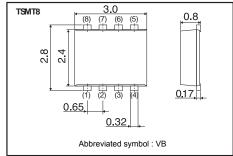
*2 Each terminal mounted on a CERAMIC Board.

• Thermal resistance

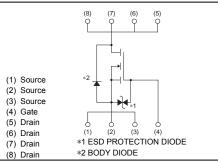
Parameter	Symbol	Limits	Unit
Channel to Ambient	Rth (ch-a)*	83.3	°C/W

* Each terminal mounted on a CERAMIC Board.

• Dimensions (Unit : mm)



Inner circuit



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• Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±10V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	20	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =20V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	0.3	-	1.0	V	V _{DS} =10V, I _D =1mA
		-	16	22		I _D =6.5A, V _{GS} =4.5V
Static drain-source on-state	р *	-	19	27		I _D =6.5A, V _{GS} =2.5V
resistance	R _{DS (on)}	-	24	32	mΩ	I _D =3.2A, V _{GS} =1.8V
		-	29	58		I _D =1.3A, V _{GS} =1.5V
Forward transfer admittance	۱ Y _{fs} ľ*	6	-	-	S	I _D =6.5A, V _{DS} =10V
Input capacitance	C _{iss}	-	870	-	pF	V _{DS} =10V
Output capacitance	C _{oss}	-	190	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	85	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	7	-	ns	I _D =3.2A, V _{DD} ≒10V
Rise time	t _r *	-	30	-	ns	V _{GS} =4.5V
Turn-off delay time	t _{d(off)} *	-	70	-	ns	R _L =3.1Ω
Fall time	t _f *	-	25	-	ns	R _G =10Ω
Total gate charge	Q _g *	-	11	-	nC	I _D =6.5A, V _{DD} ≒10V
Gate-source charge	Q _{gs} *	-	2.0	-	nC	V _{GS} =4.5V R _L =1.5Ω
Gate-drain charge	Q _{gd} *	-	2.1	-	nC	R _G =10Ω

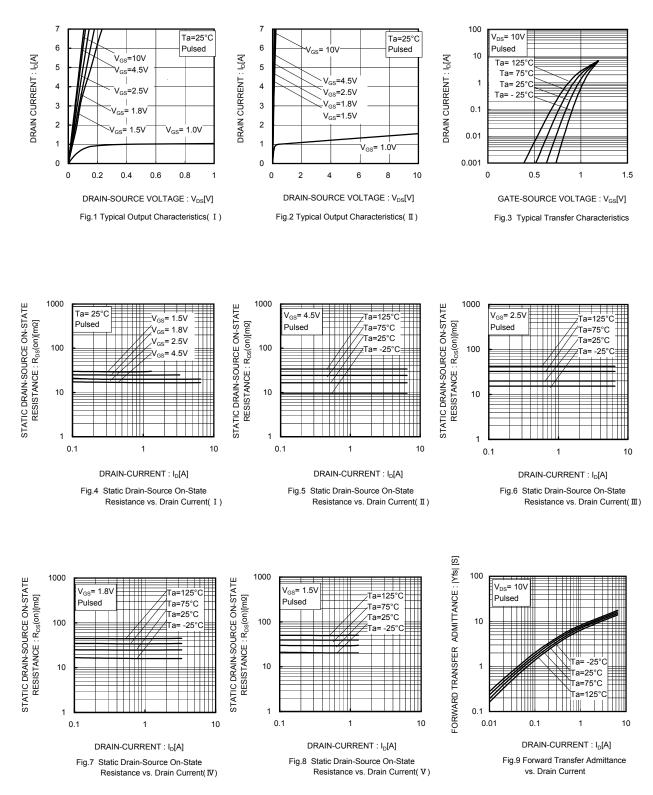
^{*}Pulsed

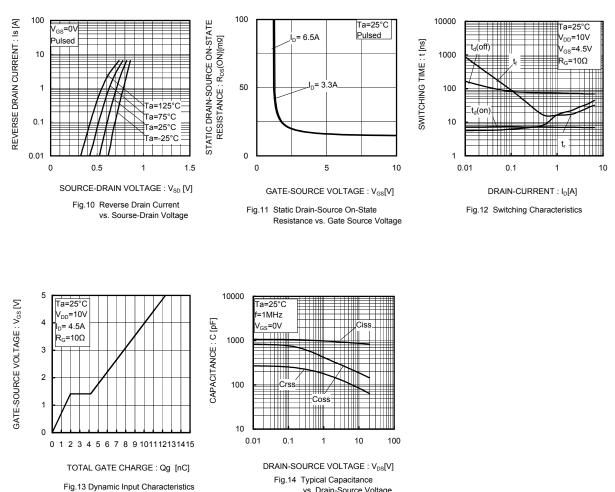
•Body diode characteristics (Source-Drain) (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward Voltage	V_{SD}^{*}	-	-	1.2	V	I _s =6.5A, V _{GS} =0V

*Pulsed

• Electrical characteristics curves





vs. Drain-Source Voltage

Measurement circuits

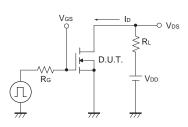


Fig.1-1 Switching time measurement circuit

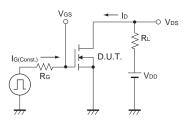


Fig.2-1 Gate charge measurement circuit

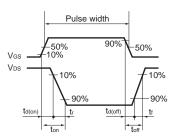


Fig.1-2 Switching waveforms

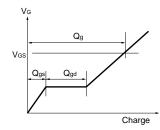


Fig.2-2 Gate Charge Waveform

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